

sumably already governed by the elastic interaction of dislocations and defects and/or other dislocations, $\delta\sigma/\sigma$ shows no dependence on work hardening. It is not unreasonable to expect, then, that in sufficiently pure material the determination of $\delta\sigma/\sigma$ in an etch-pit experiment ($\epsilon_p \simeq 0$) would yield values of V^* considerably larger than found here. Hanafee and Radcliffe³⁰ have performed etch-pitting experiments on LiF deformed under pressure and find a V^* of about $4 V_a$ for both soft crystals and hardened, "doped" crystals. They suggest that dislocation motion in LiF is limited (at $\epsilon_p \simeq 0$) by the formation of interstitials by a climbing jog. However, similar experiments on LiF

³⁰ J. E. Hanafee and S. V. Radcliffe, *J. Appl. Phys.* **38**, 4284 (1967).

performed at this laboratory³¹ give V^* approximately zero for both hard (irradiated) and soft crystals, a result in accord with the compression experiments.

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³¹ W. L. Haworth, L. A. Davis, and R. B. Gordon, *J. Appl. Phys.* **39**, 3818 (1968), this issue.